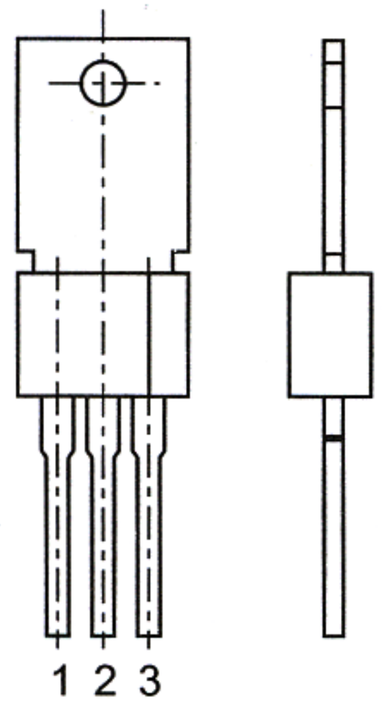
TO-202 Plastic-Encapsulate Transistors

3DA2068 TRANSISTOR(NPN)



TO-202

1.BASE

2.COLLECTOR

3.EMITTER

FEATURES

Power dissipation

P_{CM}: 1.5 W (Tamb=25℃)

Collector current

I_{CM}: 100 mA

Collector-base voltage

$V_{(BR)CBO}$: 300 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to + 150℃

ELECTRICAL CHARACTERISTICS

(Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= 100 μ A, I_E=0	300		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= 100 μ A, I_B=0	300		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= 100 μ A, I_C=0	5		V
Collector cut-off current	I_{CBO}	V_{CB}= 300 V, I_E=0		1	μ A
Emitter cut-off current	I_{EBO}	V_{EB}= 5 V, I_C=0		1	μ A
DC current gain	h_{FE}	V_{CE}= 10 V, I_C= 20 mA	40	200	
Collector-emitter saturation voltage	V_{CEsat}	I_C= 10 mA, I_B= 1 mA		1	V
Transition frequency	f_T	V_{CE}= 20 V, I_C= 20 mA f =10MHz	75		MHz

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	40-120	120-200